

# Filtering the photoluminescence spectra of atomically-thin semiconductors with Graphene

Luis Enrique Parra Lopez<sup>1</sup>

Etienne Lorchat<sup>1</sup>, Cédric Robert<sup>2</sup>, Delphine Lagarde<sup>2</sup>, Guillaume Froehlicher<sup>1</sup>, Takashi Taniguchi<sup>3</sup>, Kenji Watanabe<sup>3</sup>, Xavier Marie<sup>2,4</sup> and Stéphane Berciaud<sup>1,4</sup>

<sup>1</sup>Université de Strasbourg, CNRS, Institut de Physique et Chimie des Matériaux de Strasbourg, UMR 7504, F-67000 Strasbourg, France.

<sup>2</sup>Université de Toulouse, INSA-CNRS-UPS, LPCNO, 135 Avenue de Rangueil, 31077, Toulouse, France.

<sup>3</sup>National Institute for Materials Science, Tsukuba, Ibaraki 305-0044, Japan.

<sup>4</sup>Institut Universitaire de France, 1 rue Descartes, 75231 Paris cedex 05, France.

[luis.parralopez@ipcms.unistra.fr](mailto:luis.parralopez@ipcms.unistra.fr)

Atomically thin semiconductors made from transition metal dichalcogenides are appealing material systems for the investigation of strong light-matter interactions and are ideal building blocks for an increasing number of applications in nanophotonics, optoelectronics and valley-tronics [1]. However, atomically-thin TMDs exhibit quite complex excitonic manifolds and their emission spectra are often composed of a large number of features that are challenging to decipher [2-4]. On a practical level, implementations in photonic devices would profit from the existence of a prominent single emission line. Here we demonstrate that an atomically thin-semiconductor stacked onto a graphene monolayer enables single narrow-line photoluminescence (1.7 meV) arising solely from neutral excitons [5]. This filtering effect comes from a neutralization of the TMD combined to selective energy transfer of long-lived excitonic species to graphene. Interestingly our observations are valid both on bright (Mo-based) and dark (W-based) TMDs monolayers. Our results establish TMD/Graphene heterostructures as a suitable building block for opto-electronics.

## References

[1] K. F. Mak, J. Shan. *Nature Nanotech.* 10, 216 (2016).

[2] M. Barbone et al. *Nature Communications*, 9, 3721 (2018).

[3] D. Vaclavkova et al. *Nanotechnology* 29 (2018) 325705.

[4] E. Courtade et al. *Phys. Rev. B* 96, 085302 (2017)

[5] **L. Parra Lopez** et al. arXiv:1908.10690 (Accepted for publication in *Nature Nanotech.*)

## Figures

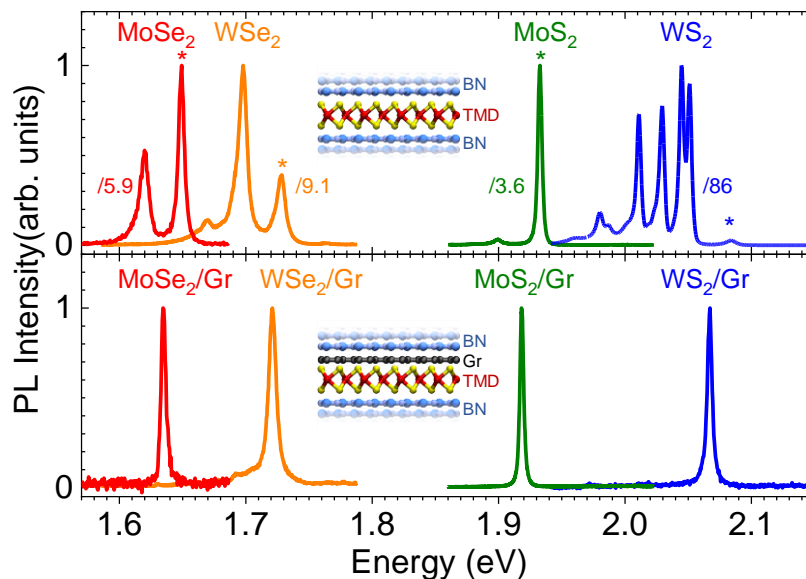


Figure 1: Bright, single narrow-line photoluminescence spectra of BN-Capped monolayer TMD/Graphene heterostructures (bottom). The PL of the BN-Capped TMD regions are shown on the upper panel for comparison.